

Title (en)

TANTALUM SPUTTERING TARGET AND METHOD OF MANUFACTURE

Title (de)

TANTALSPUTTERTARGETS UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)

CIBLE DE PULVERISATION CATHODIQUE DE TANTALE ET PROCEDE DE FABRICATION DE LADITE CIBLE

Publication

**EP 1090153 A4 20010905 (EN)**

Application

**EP 99925908 A 19990526**

Priority

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- US 8686898 P 19980527
- US 31677799 A 19990521

Abstract (en)

[origin: WO9961670A1] Described is a method for producing high purity tantalum, the high purity tantalum so produced and sputtering targets of high purity tantalum. The method involves purifying starting materials followed by subsequent refining into high purity tantalum.

IPC 1-7

**C22B 34/24; C23C 14/34; C22B 3/44; C01G 35/00; C01G 35/02**

IPC 8 full level

**B22F 1/00** (2022.01); **C01G 35/00** (2006.01); **C22B 3/04** (2006.01); **C22B 5/00** (2006.01); **C22B 5/04** (2006.01); **C22B 9/22** (2006.01);  
**C22B 34/24** (2006.01); **C22C 27/02** (2006.01); **C23C 14/14** (2006.01); **C23C 14/34** (2006.01)

CPC (source: EP KR US)

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**B22F 2999/00** (2013.01 - EP US); **Y10S 438/923** (2013.01 - EP US); **Y10S 438/968** (2013.01 - EP US)

Citation (search report)

- [XY] DE 3790259 T1 19880623
- [Y] US 5635146 A 19970603 - SINGH RAJ P [US], et al
- [YAX] PATENT ABSTRACTS OF JAPAN vol. 015, no. 461 (C - 0887) 22 November 1991 (1991-11-22)
- See references of WO 9961670A1

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KR 20010071334 A 20010728; US 2002132388 A1 20020919; US 2003082864 A1 20030501; US 2005284259 A1 20051229;  
US 2005284546 A1 20051229; US 6323055 B1 20011127; US 6566161 B1 20030520; US 6955938 B2 20051018; US 6958257 B2 20051025;  
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JP 2000551050 A 19990526; KR 20007013343 A 20001127; US 19615605 A 20050803; US 20274305 A 20050812; US 22988802 A 20020827;  
US 31677799 A 19990521; US 5320102 A 20020115; US 71747600 A 20001120